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Text of the abstract

It is disclosed a photoresist cleaning composition for stripping a photoresist pattern having a film thickness of 3-150 μm , which contains (a) a quaternary ammonium hydroxide including tetramethyl ammonium hydroxide and tetraethyl ammonium hydroxide, (b) a mixture of water-soluble organic solvents comprising dimethylsulfoxide (DMSO), sulfolane or dimethylsulfone and at least an additional organic solvent, (c) at least one corrosion inhibitor including polyethylenimine (PEI) and (d) water. A method for treating a substrate therewith is also disclosed.